

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In the Claims.

1. (Amended) A method, comprising:

5 varying a dopant supply rate for a doped insulating layer according to a
 variation in temperature of a substrate on which the doped insulating layer is
 being formed; and

 varying the dopant supply rate includes increasing the dopant supply
 rate as the substrate temperature increases.

Please cancel claim 6.

11. (Amended) A method, comprising:

10 compensating for a temperature dependent dopant gradient in a doped
 insulating film comprising silicon oxide having a phosphorous concentration
 greater than about 7% by weight, by varying a dopant supply rate as the doped
 insulating film is formed.

Please cancel claim 12.

15 13. (Amended) The method of claim 11, wherein:

 the dopant supply rate is varied for an initial thickness of the doped
 insulating film to compensate for variations in a substrate temperature.